2SA1121

Silicon PNP Epitaxial

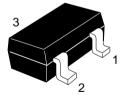
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Application

- Low frequency amplifier
- Complementary pair with 2SC2618

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector



2SA1121

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-35	V
Collector to emitter voltage	V _{CEO}	– 35	V
Emitter to base voltage	V_{EBO}	-4	V
Collector current	I _c	-500	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Тј	150	°C
Storage temperature	Tstg	-55 to +150	°C

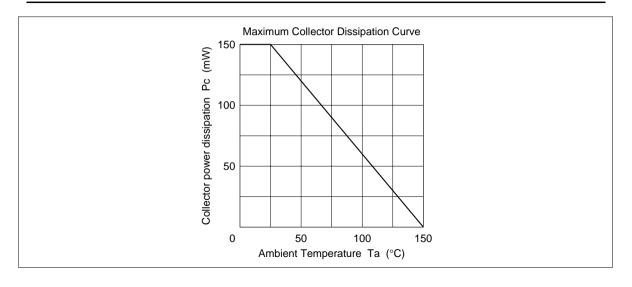
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-35	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-35	_	-	V	$I_{C} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-4	_	_	V	$I_E = -10 \ \mu A, \ I_C = 0$
Collector cutoff current	I _{CBO}	_	_	-0.5	μΑ	$V_{CB} = -20 \text{ V}, I_{E} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	-0.2	-0.6	V	$I_{\rm C} = -150 \text{ mA}, I_{\rm B} = -15 \text{ mA}$
DC current transfer ratio	h _{FE} *1	60	_	320		$V_{CE} = -3 \text{ V}, I_{C} = -10 \text{ mA}$
	h _{FE}	10	_	_		$V_{CE} = -3 \text{ V}, I_{C} = -500 \text{ mA}$ (Pulse test)
Base to emitter voltage	V_{BE}		-0.64	_	V	$V_{CE} = -3 \text{ V}, I_{C} = -10 \text{ mA}$

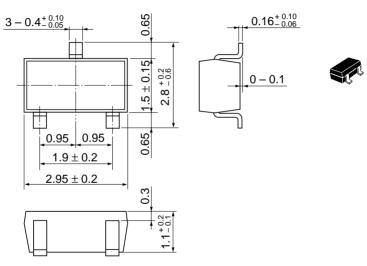
Note: 1. The 2SA1121 is grouped by h_{FE} as follows.

Grade	В	С	D
Mark	SB	SC	SD
h _{FE}	60 to 120	100 to 200	160 to 320

See characteristic curves of 2SA673.



Unit: mm



Hitachi Code	MPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.011 g

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